

Transistor

DC-DC Converter (-30V, -3.5A)

RSQ035P03

●Features

- 1) Low On-resistance.(65mΩ at 4.5V)
- 2) High Power Package.
- 3) High speed switching.
- 4) Low voltage drive.(4.5V)

●Applications

DC-DC converter

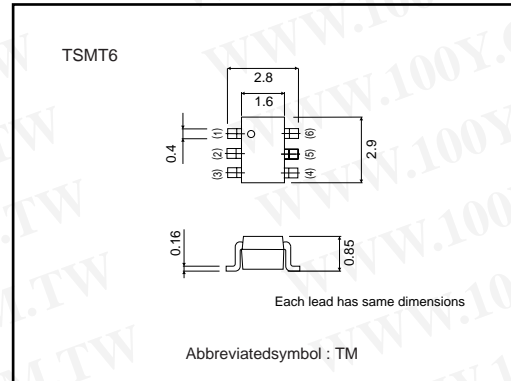
●Structure

Silicon P-channel
MOSFET

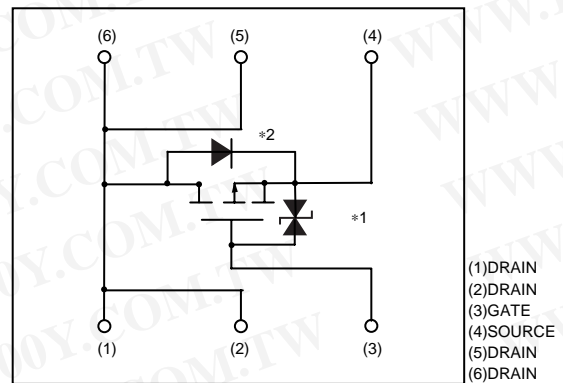
●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RSQ035P03		○

●External dimensions (Units : mm)



●Equivalent circuit



- *1 ESD PROTECTION DIODE
 *2 BODY DIODE

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●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	-30	V
Gate-source voltage	V _{GSS}	±20	V
Drain current	Continuous	I _D	±3.5 A
	Pulsed	I _{DP}	±14 A *1
Source current (Body diode)	Continuous	I _S	-1 A
	Pulsed	I _{SP}	-4 A *1
Total power dissipation	P _D	1.25	W*2
Channel temperature	T _{ch}	150	°C
Range of Strage temperature	T _{stg}	-55~+150	°C

*1 Pw≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	-30	-	-	V	I _D =-1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	-1	μA	V _{DS} =-30V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	-1.0	-	-2.5	V	V _{DS} =-10V, I _D =-1mA
Static drain-source on-state resistance	R _{DS(on)} * ¹	-	45	65	mΩ	I _D =-3.5A, V _{GS} =-10V
		-	65	90	mΩ	I _D =-3.5A, V _{GS} =-4.5V
		-	70	95	mΩ	I _D =-1.75A, V _{GS} =-4.0V
Forward transfer admittance	Y _{fs} * ²	2.0	-	-	S	V _{DS} =-10V, I _D =-1.75mA
Input capacitance	C _{iss}	-	780	-	pF	V _{DS} =-10V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}	-	180	-	pF	
Reverse transfer capacitance	C _{rss}	-	130	-	pF	
Turn-on delay time	t _{d(on)} * ³	-	15	-	ns	I _D =-1.75A V _{DD} =-15V V _{GS} =-10V R _L =8.6Ω R _{GS} =10Ω
Rise time	t _r * ⁴	-	35	-	ns	
Turn-off delay time	t _{d(off)} * ⁵	-	45	-	ns	
Fall time	t _f * ⁶	-	25	-	ns	
Total gate charge	Q _g	-	9.2	-	nC	V _{DD} =-15V V _{GS} =-5V I _D =-3.5mA
Gate-source charge	Q _{gs}	-	2.2	-	nC	
Gate-drain charge	Q _{gd}	-	3.4	-	nC	

*PULSED

Body diode characteristics (source-drain characteristics)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	-	-	-1.2	V	I _S =-1A, V _{GS} =0V

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●Electrical characteristic curves

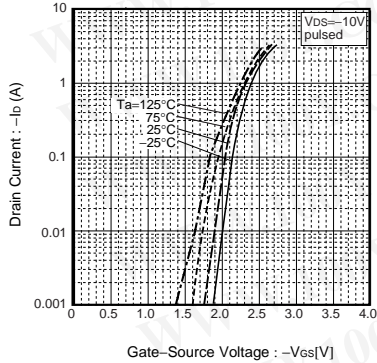


Fig.1 Typical Transfer Characteristics

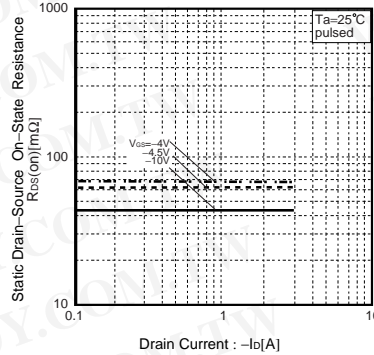


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

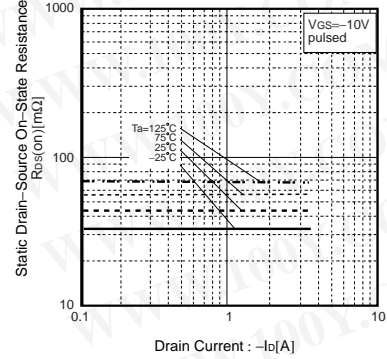


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

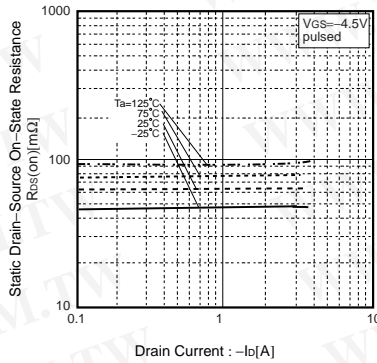


Fig.4 Static Drain-Source On-State Resistance vs. Drain-Current

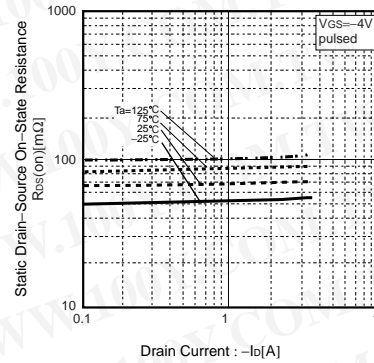


Fig.5 Static Drain-Source On-State Resistance vs. Drain-Current

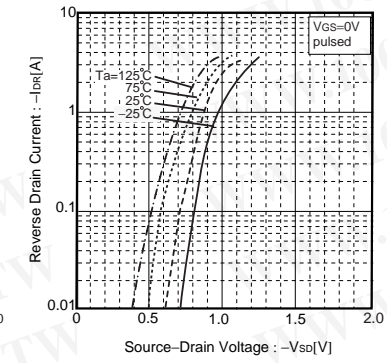


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

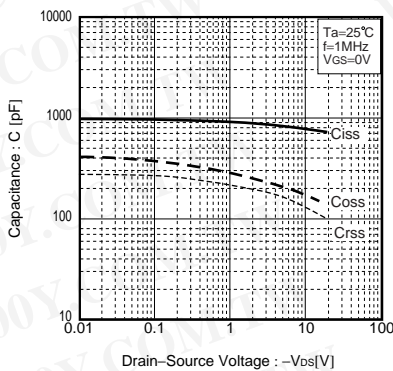


Fig.7 Typical Capacitance vs. Drain-Source Voltage

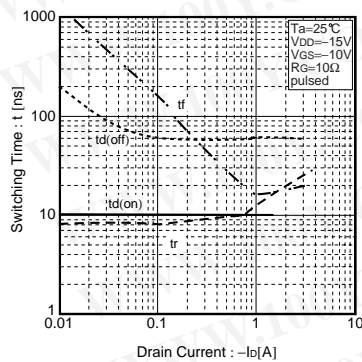


Fig.8 Switching Characteristics

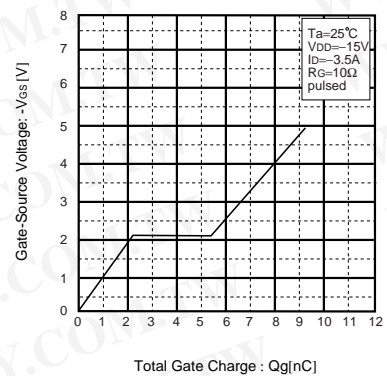


Fig.9 Dynamic Input Characteristics

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● Measurement circuits

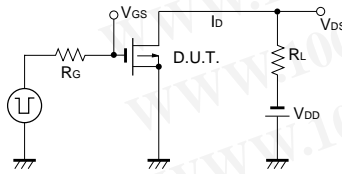


Fig.10 Switching Time Measurement Circuit

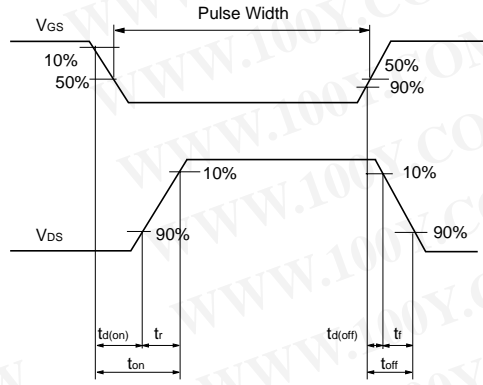


Fig.11 Switching Waveforms

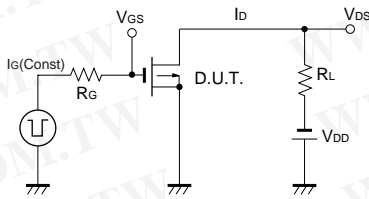


Fig.12 Gate Charge Measurement Circuit

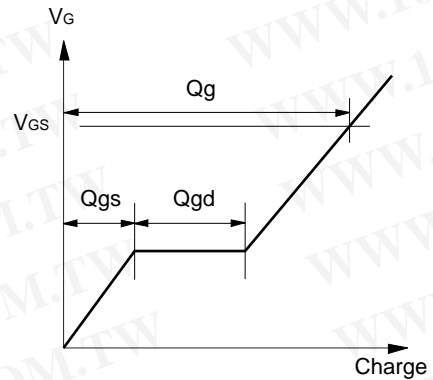


Fig.13 Gate Charge Waveforms

Appendix

Notes

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